

140 mW Power Amplifier with T/R Switch 2.4 - 2.5 GHz

AM55-0007

Features

- Highly Integrated PA/Attenuator and T/R Switch
- Low Current Consumption: 120 mA Typ.
- Switch and Attenuator Controls CMOS Compatible
- High Power (140 mW) and Low Power (16 mW) Transmit Power Control
- +5 V/-5 V Fixed Supply Voltages

Description

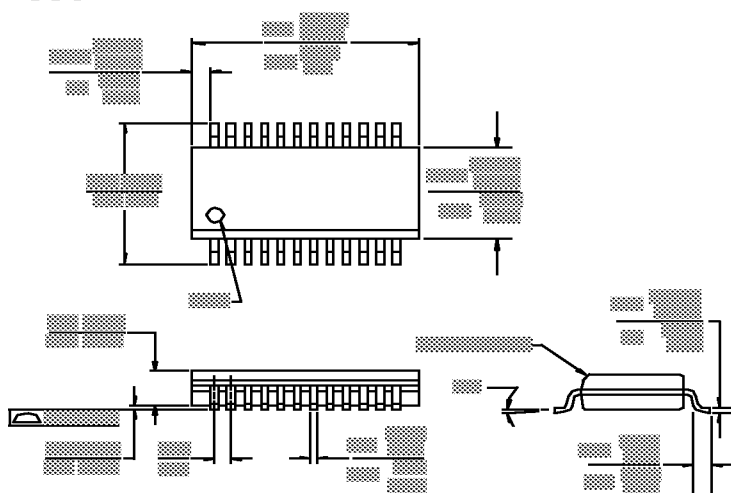
M/A-COM's AM55-0007 is a GaAs power amplifier with an integrated transmit/receive switch in a low cost SSOP 24 plastic package. The AM55-0007 employs active bias circuits that eliminate the need for external bias adjustment. A 'Sleep Mode' is incorporated which turns off current draw from the positive supply of the PA during receive mode. The AM55-0007 provides a 10-dB step attenuator for use as a transmit power controller.

The AM55-0007 is designed for low power consumption and is ideally suited for FSK systems in the 2.4 - 2.5 GHz bands (North American ISM, Japanese RCR.32 and European ETSI). Typical applications include WLAN and wireless portable data collection.

This amplifier is also available with diversity switching (AM55-0001). Either power amplifier can be combined with a transceiver IC (MD58-0001) to form a complete RF front end.

M/A-COM's AM55-0007 is fabricated using a mature 0.5-micron gate length GaAs process. The process features full passivation for increased performance and reliability.

SSOP-24



Dimensions are in inches over millimeters.

Ordering Information

| Part Number | Description |
|--------------|------------------------------|
| AM55-0007 | SSOP 24-Lead Plastic Package |
| AM55-0007TR | Forward Tape & Reel * |
| AM55-0007RTR | Reverse Tape & Reel * |
| AM55-0007SMB | Designer's Kit |

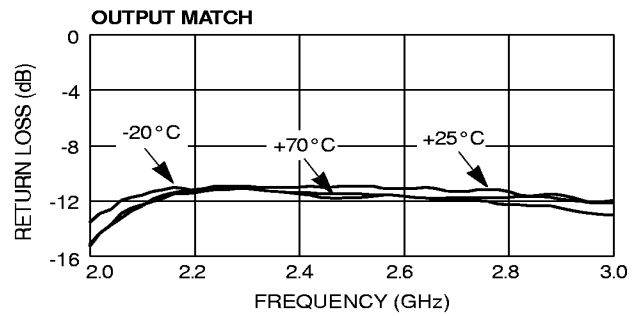
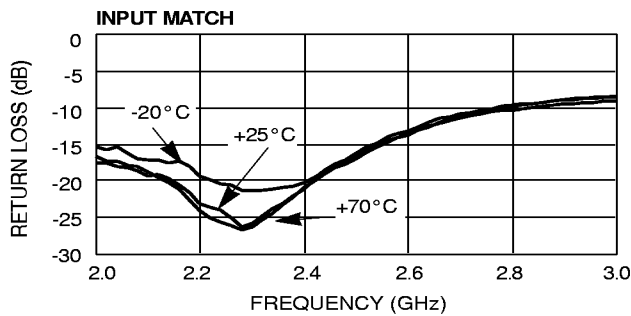
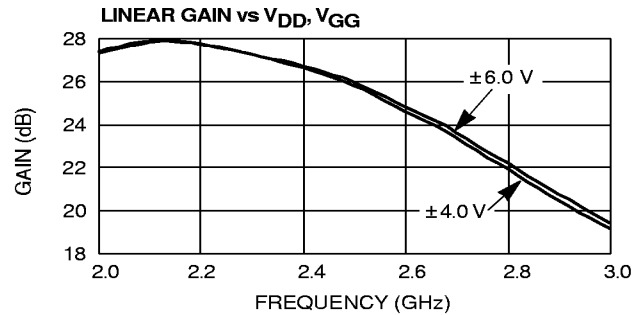
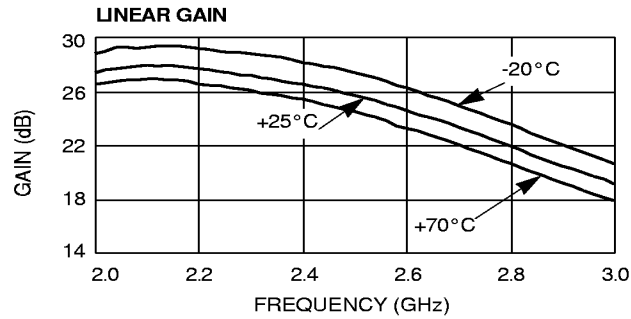
* If specific reel size is required, consult factory for part number assignment.

Typical Electrical Specifications

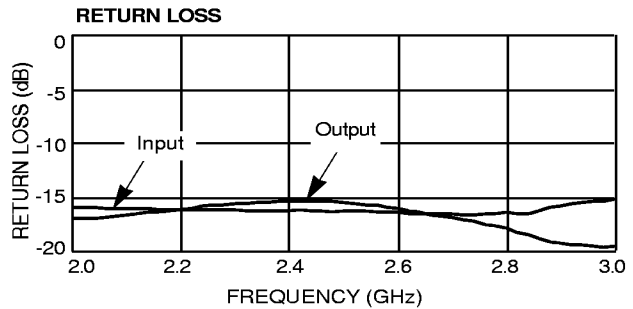
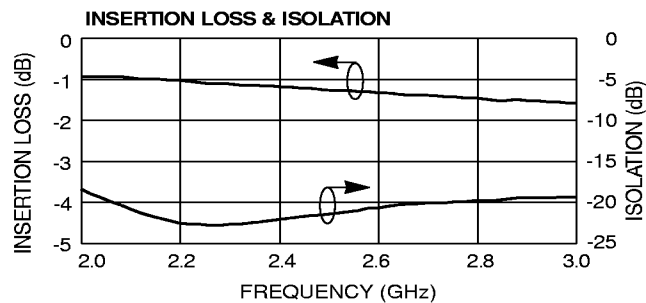
Test Conditions: Frequency: 2.45 GHz, $V_{DD} = 5\text{ V} \pm 5\%$, $V_{GG} = -5\text{ V} \pm 5\%$, $T_A = +25^\circ\text{C}$

| Parameter | Test Conditions | Units | Min. | Typ. | Max. |
|---|--|-------|------|-------|------|
| Power Amplifier | | | | | |
| Linear Gain | High Power Mode | dB | 23 | 26.5 | |
| | Low Power Mode | dB | 12 | 16 | |
| VSWR In | Both Modes | | | 1.5:1 | |
| Output Power | $P_{IN} = -3\text{ dBm}$ High Power Mode | dBm | 19 | 21.5 | |
| | Low Power Mode | dBm | 8 | 12 | |
| Second Harmonic | $P_{IN} = -3\text{ dBm}$ High Power Mode | dBc | | -25 | |
| Third Harmonic | | dBc | | -17 | |
| $I_{DD} (V_{DD1} + V_{DD2} + V_{DD\text{ PA}})$ | | mA | | 120 | 200 |
| T/R Switch | | | | | |
| Insertion Loss | | dB | | 1.2 | |
| Isolation | | dB | 10 | 15 | |
| VSWR In/Out | | | | 1.5:1 | |

Small Signal Power Amplifier¹

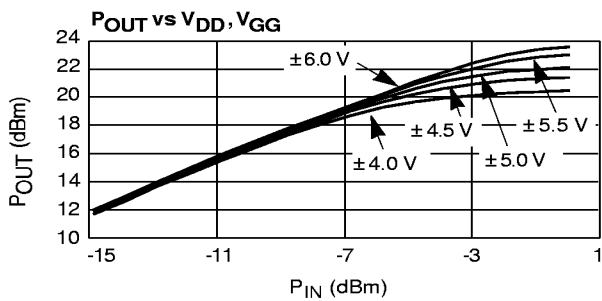
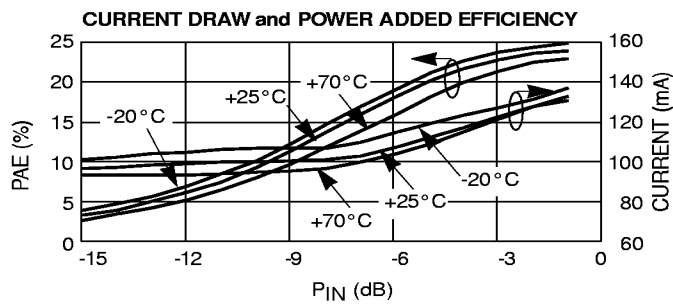
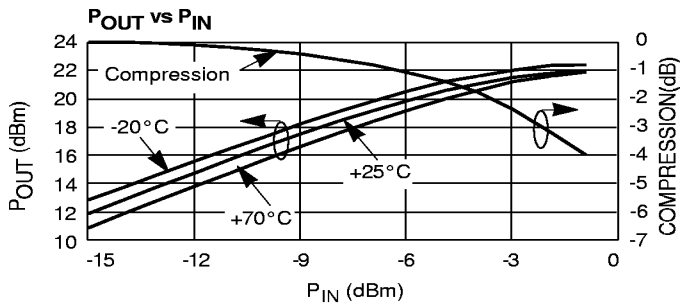


T/R Switch Small Signal Performance¹



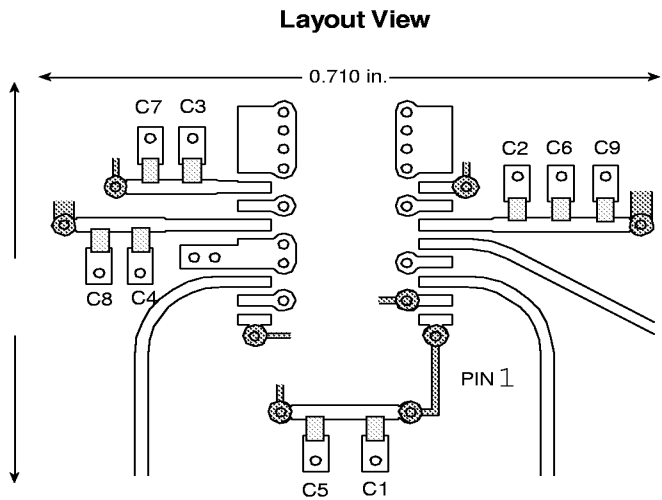
1. Unless otherwise noted, Frequency: 2.45 GHz, $V_{DD} = 5 \text{ V} \pm 5\%$, $V_{GG} = -5 \text{ V} \pm 5\%$, $T_A = +25^\circ\text{C}$

Power Amplifier Power Performance¹

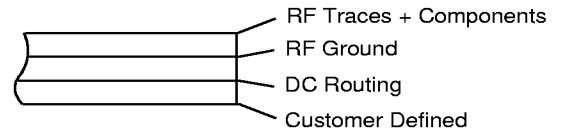


1. Unless otherwise noted, Frequency: 2.45 GHz, V_{DD} = 5 V ±5%, V_{GG} = - 5 V ±5%, T_A = +25°C

Recommended PCB Configuration



Cross-Section View



The PCB dielectric between RF traces and RF ground layers should be chosen to reduce RF discontinuities between 50- Ω lines and package pins. M/A-COM recommends an FR-4 dielectric thickness of 0.008 in. (0.2 mm), yielding a 50- Ω line width of 0.015 in. (0.38 mm). The recommended metalization thickness is 1 oz. copper.

Shaded traces are vias to DC routing layer and traces on DC routing layer.

External Circuitry Parts List

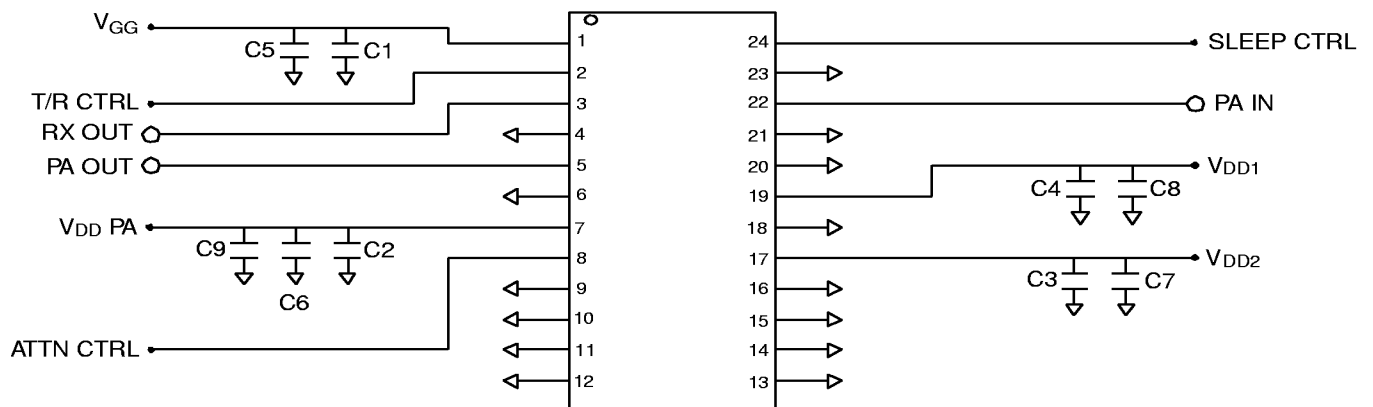
| Label | Value | Purpose |
|---------|--------------|--------------|
| C1 - C4 | 33 pF | Bypass (GHz) |
| C5 - C8 | 220 pF | Bypass (MHz) |
| C9 | 0.01 μ F | Bypass (kHz) |

All off-chip components are low-cost surface mount components obtainable from multiple sources. (0.020 in.x 0.040 in.or 0.030 in.x 0.050 in.)

Biasing Procedure

The AM55-0007 requires the V_{GG} bias be applied prior to *any* V_{DD} bias. Permanent damage may occur if this procedure is not followed. All FETs in the PA will draw excessive current and damage internal circuitry.

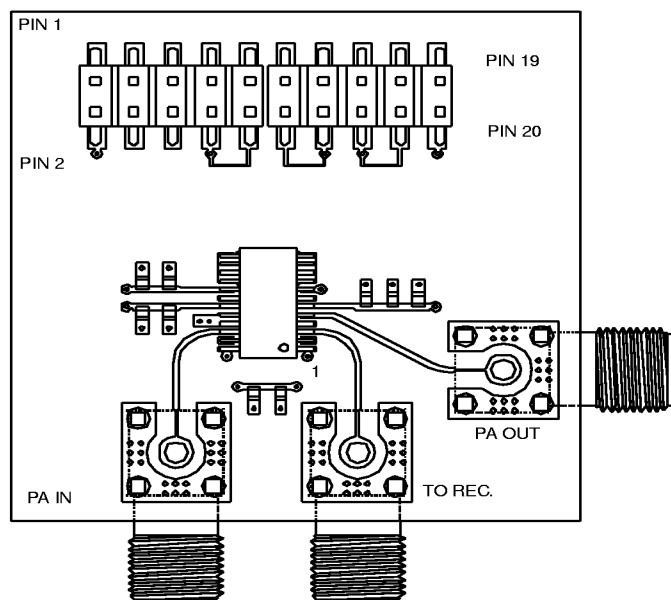
External Circuitry



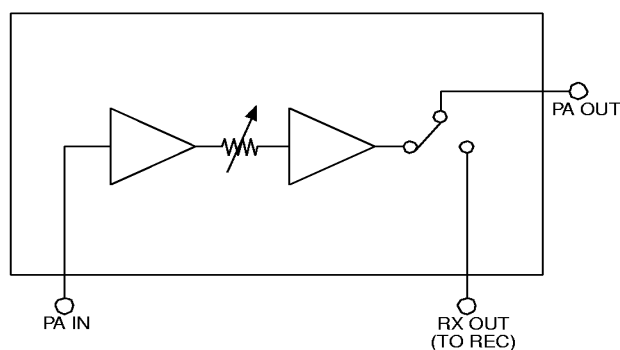
Designer's Kit (AM55-0007SMB)

The AM55-0007SMB Designer's Kit allows for immediate evaluation of M/A-COM's AM55-0007 integrated Power Amplifier with T/R and Diversity Switch. The evaluation board consists of an AM55-0007, recommended external surface mount circuitry, RF connectors and a DC multi-pin connector, all mounted to a multi-layer FR-4 PCB. Other items included in the Designer's Kit: a floppy disk (with typical performance data and a .DXF file of the recommended PCB layout) and any additional Application Notes. The AM55-0007SMB evaluation PCB and block diagram are illustrated below with all functional ports labeled.

P/A Switch Sample Board



Functional Block Diagram

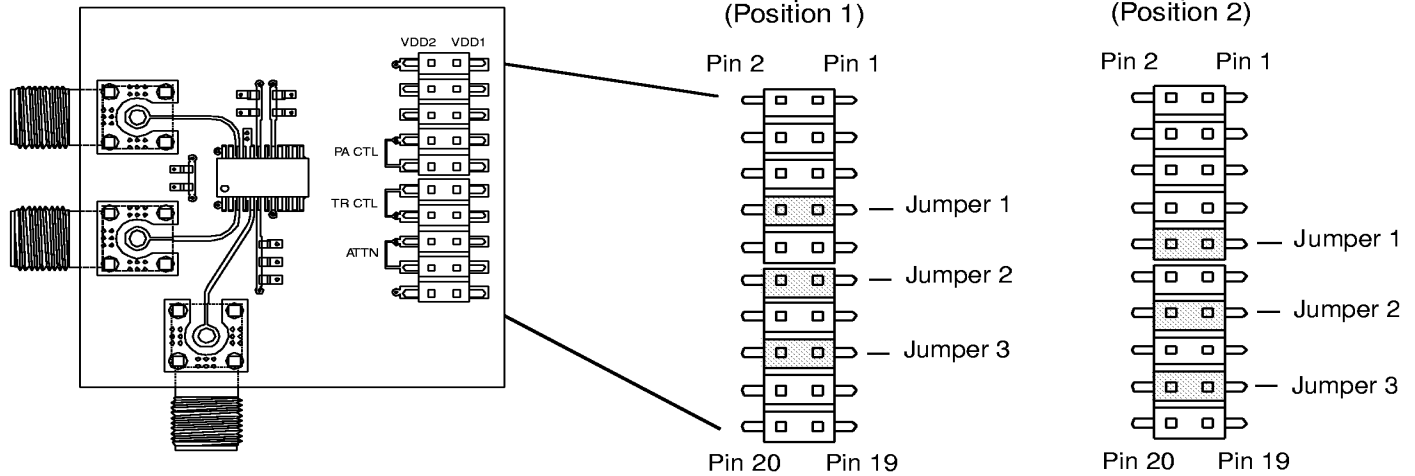


DC Connector Pinout

| PCB DC Connector | Function | Device Pin Number |
|------------------|---------------------------------|-------------------|
| 1 | V_{DD1} (+ 5 V) | 19 |
| 2 | V_{DD2} (+ 5 V) | 17 |
| 3 | N/C | N/C |
| 4 | N/C | N/C |
| 5 | N/C | N/C |
| 6 | N/C | N/C |
| 7 | Negative Logic High (GND) | N/C |
| 8 | PA Control (0 V/-5 V) | 24 |
| 9 | Negative Logic Low (V_{GG}) | 1 |
| 10 | PA Control (0 V/-5 V) | 24 |

| PCB DC Connector | Function | Device Pin Number |
|------------------|--------------------------|-------------------|
| 11 | Logic High (V_{DD1}) | 19 |
| 12 | T/R Control (0 V/+5 V) | 2 |
| 13 | Logic Low (GND) | N/C |
| 14 | T/R Control (0 V/+5 V) | 2 |
| 15 | Logic High (V_{DD1}) | 19 |
| 16 | ATTN Control (0 V/+5 V) | 8 |
| 17 | Logic Low (GND) | N/C |
| 18 | ATTN Control (0 V/+5 V) | 8 |
| 19 | V_{DD} PA (+5 V) | 6 |
| 20 | V_{GG} (- 5 V) | 1 |

PCB DC Connector Jumper Settings



Jumper 1 (PA Sleep Control)

Position 1 = PA ON
Position 2 = PA Sleep Mode

Jumper 2 (T/R Switch Control)

Position 1 = Receive Mode
Position 2 = Transmit Mode

Jumper 3 (Attenuator Control)

Position 1 = Attenuator ON (Low Power Transmit)
Position 2 = Attenuator OFF (High Power Transmit)

AM55-0007SMB Biasing Procedure

In order to prevent transients which may damage the MMIC, please adhere to the following procedure.

- Turn on all power supplies and set all voltages to 0 volts BEFORE connecting the power supplies to the DC connector.
- Set jumpers for desired test mode.
- Apply a -5.0 volt supply to DC connector pin 20 (V_{GG}).
- Apply a +5.0 volt supply to the DC connector pin 1 (V_{DD1}).
- Apply a +5.0 volt supply to the DC connector pin 2 (V_{DD2}).
- Apply a +5.0 volt supply to the DC connector pin 19 (V_{DD} PA).
- Adjust V_{GG} supply to -5 volts.
- Adjust all V_{DD} supplies to +5 volts.
- Hot switching of jumpers will not damage device.
- To power off, reverse above procedure.
 1. Set V_{DD1} & V_{DD2} & V_{DD} PA to 0 volts.
 2. Set V_{GG} to 0 volts.
 3. Disconnect bias lines from DC connector.
 4. Turn off power supplies.

Evaluation PCB and RF Connector Losses

| Port Reference | Approximate Loss (dB) |
|-----------------|-----------------------|
| PA IN | 0.25 |
| PA OUT | 0.25 |
| Rx OUT (TO REC) | 0.25 |

The DC connector on the Designer's Kit PCB allows selection of all the device's operating modes. It is accomplished by one or more of the following methods:

1. A mating female multi-pin connector (Newark Electronics Stock # 46F-4658, not included)
2. Wires soldered to the necessary pins (not included)
3. Clip leads (not included)
4. A combination of clip leads or wires and jumpers (jumpers included as required)